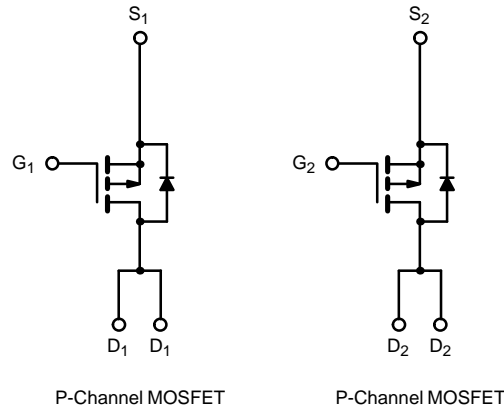
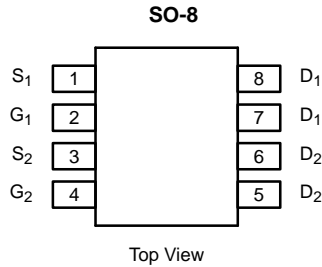




Dual P-Channel 2.5-V (G-S) MOSFET

2.5-V Rated

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.05 @ $V_{GS} = -4.5$ V	± 5
	0.074 @ $V_{GS} = -2.5$ V	± 4.1



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-12	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	± 5	A
	$T_A = 70^\circ\text{C}$		± 4.0	
Pulsed Drain Current		I_{DM}	± 20	
Continuous Source Current (Diode Conduction) ^a		I_S	-1.7	
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	2.0	W
	$T_A = 70^\circ\text{C}$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>



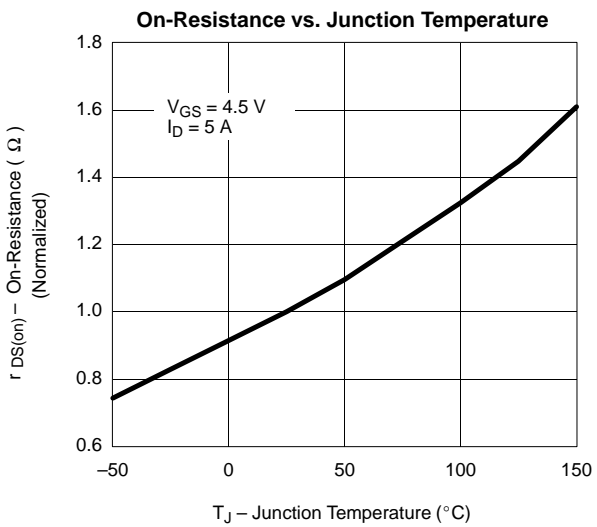
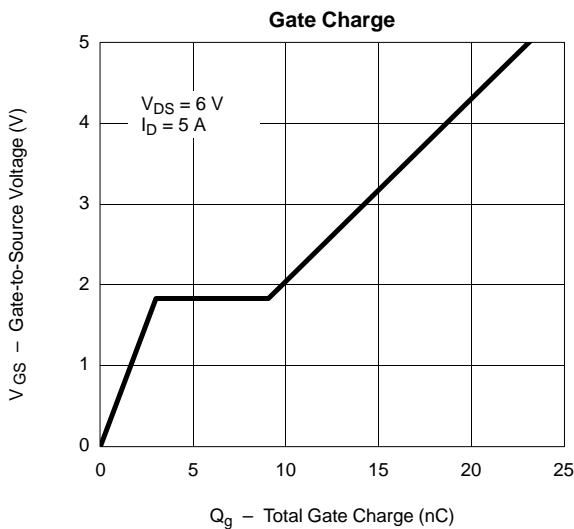
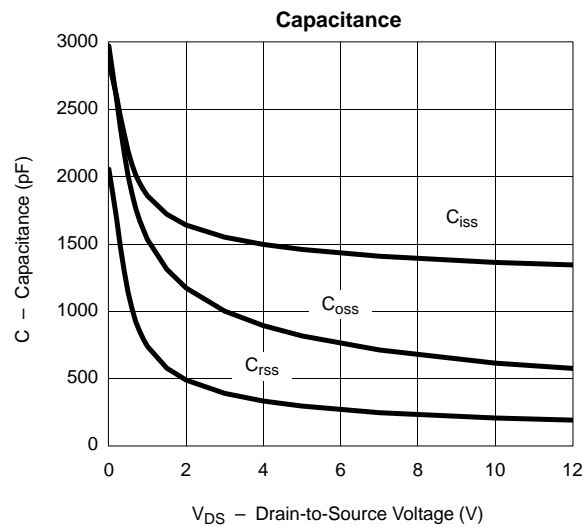
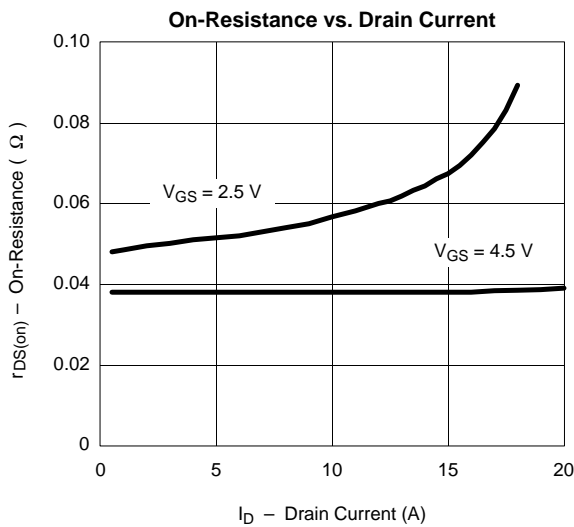
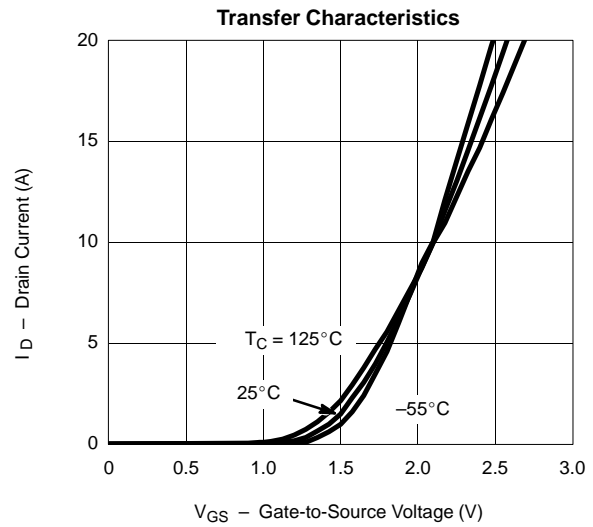
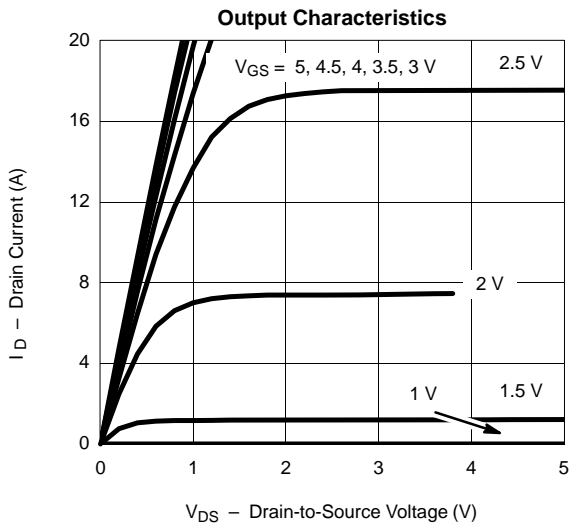
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static—0.6						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.6			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -12 V, V _{GS} = 0 V, T _J = 55°C			-5	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = -4.5 V	-20			A
		V _{DS} ≥ 5 V, V _{GS} = -2.5 V	-6			
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -5 A		0.039	0.05	Ω
		V _{GS} = -2.5 V, I _D = -3 A		0.051	0.074	
Forward Transconductance ^b	g _{fs}	V _{DS} = -9 V, I _D = -5 A		16		S
Diode Forward Voltage ^b	V _{SD}	I _S = -1.7 A, V _{GS} = 0 V		-0.75	-1.2	V
Dynamic^a						
Total Gate Charge	Q _g	V _{DS} = -6 V, V _{GS} = -4.5 V, I _D = -5 A		21	40	nC
Gate-Source Charge	Q _{gs}			3		
Gate-Drain Charge	Q _{gd}			6		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6 V, R _L = 6 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		20	40	ns
Rise Time	t _r			40	80	
Turn-Off Delay Time	t _{d(off)}			100	200	
Fall Time	t _f			60	120	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = -1.7 A, di/dt = 100 A/μs		67	100	

Notes

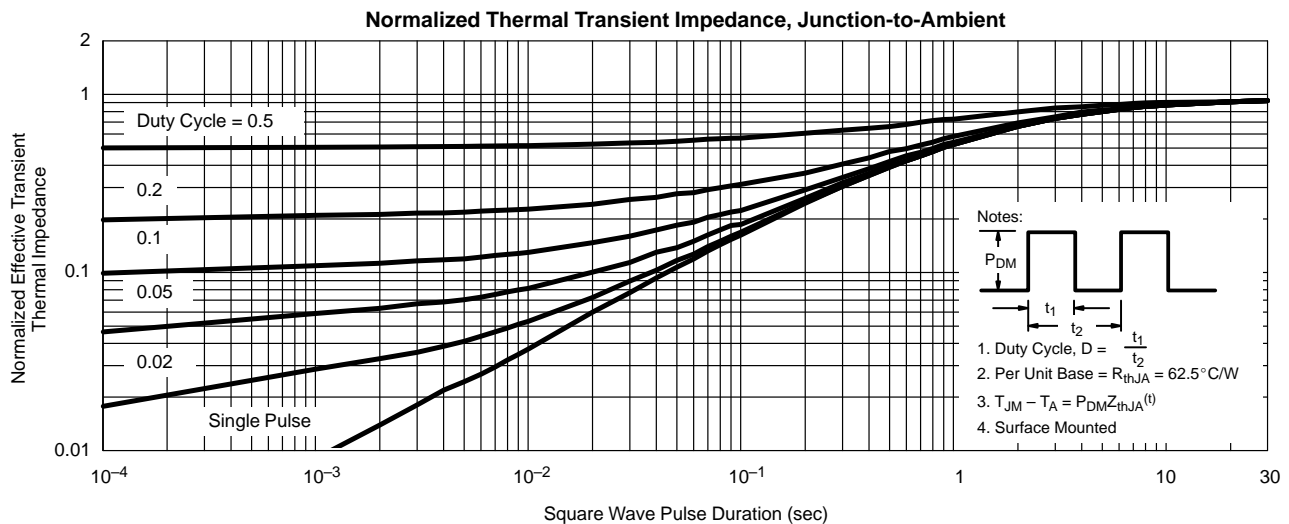
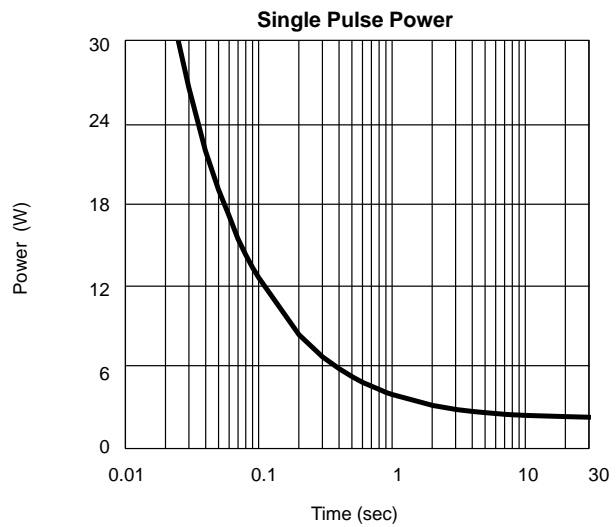
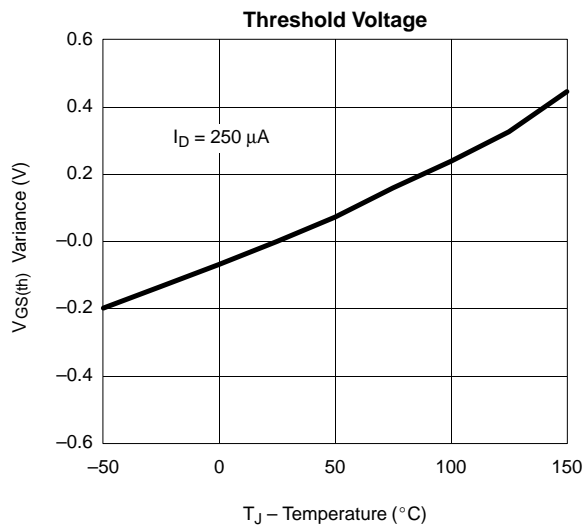
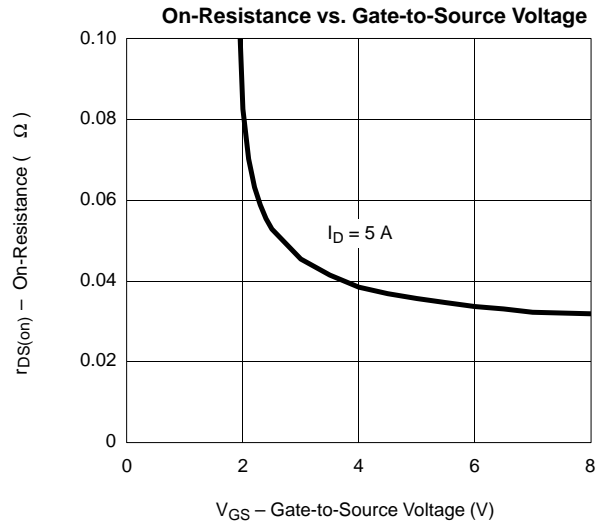
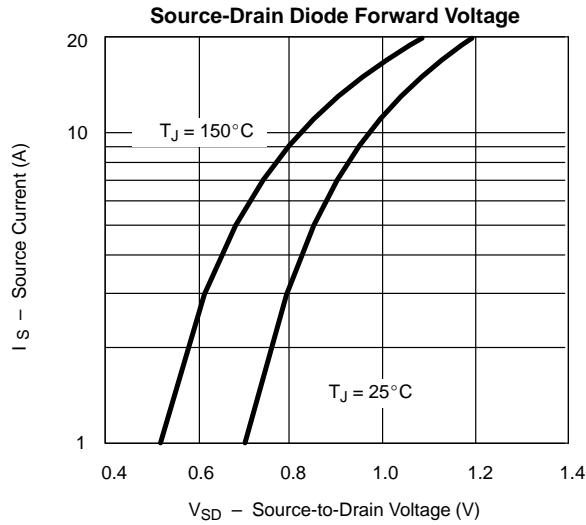
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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